

Shunpei Yamazaki

List of Publications by Year in descending order

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46
papers

797
citations

567281

15
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526287

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times ranked

441
citing authors

#	ARTICLE	IF	CITATIONS
1	9â€¹: Evaluation of Xâ€ray Resistance of Submicronâ€Size <i>c</i> â€Axis Aligned Crystallineâ€Oxide Semiconductor. Digest of Technical Papers SID International Symposium, 2022, 53, 78-81.	0.3	1
2	5,291â€ppi OLED display enabled by monolithic integration of <i>c</i>â€axisâ€aligned crystalline IGZO FET and Si CMOS. Journal of the Society for Information Display, 2022, 30, 690-698.	2.1	5
3	A Compact Physics-Based Charge Core Model for CAAC In-Ga-Zn Oxide Multi-Gate FETs. , 2021, , .		2
4	(Invited) Crystalline Oxide Semiconductor Applicable to Low-Power Consumption Edge AI. ECS Transactions, 2021, 102, 3-18.	0.5	3
5	(Invited) Crystalline Oxide Semiconductor Applicable to Low-Power Consumption Edge AI. ECS Meeting Abstracts, 2021, MA2021-01, 993-993.	0.0	0
6	14â€²: Invited Paper: OLED Display Incorporating an Organic Image Sensor. Digest of Technical Papers SID International Symposium, 2020, 51, 180-183.	0.3	0
7	TCAD Simulation of a 3D NAND Memory Utilizing In-Ga-Zn-Oxide: "3D OS NAND" with 4 V Drive, High Endurance and Density. ECS Transactions, 2020, 98, 55-67.	0.5	1
8	Characteristics and Applications of CAAC-IGZO FET with Gate Length of 13nm. ECS Transactions, 2020, 98, 13-27.	0.5	4
9	(Invited) Display and LSI Applications of Oxide Semiconductor LSIs (OS LSIs) Using Crystalline Inâ€Gaâ€Zn Oxide (IGZO): Applications Related to Coronavirus COVID-19 Pandemic. ECS Transactions, 2020, 98, 185-204.	0.5	1
10	TCAD Simulation of a 3D NAND Memory Utilizing In-Ga-Zn-Oxide: "3D OS NAND" with 4 V Drive, High Endurance and Density. ECS Meeting Abstracts, 2020, MA2020-02, 1921-1921.	0.0	0
11	Characteristics and Applications of CAAC-IGZO FET with Gate Length of 13nm. ECS Meeting Abstracts, 2020, MA2020-02, 1914-1914.	0.0	0
12	(Invited) Display and LSI Applications of Oxide Semiconductor LSIs (OS LSIs) Using Crystalline Inâ€Gaâ€Zn Oxide (IGZO): Applications Related to Coronavirus COVID-19 Pandemic. ECS Meeting Abstracts, 2020, MA2020-02, 1941-1941.	0.0	0
13	A 5291â€ppi organic lightâ€emitting diode display using fieldâ€effect transistors including a câ€axis aligned crystalline oxide semiconductor. Journal of the Society for Information Display, 2019, 27, 497-506.	2.1	15
14	37â€¹: Liquid Crystal Display Panel with a Pixel Including Oxide Semiconductor Fieldâ€Effect Transistor Memory (Pixel AI). Digest of Technical Papers SID International Symposium, 2019, 50, 512-515.	0.3	0
15	71â€²: Distinguished Paper: OLED Display Incorporating Organic Image Sensor. Digest of Technical Papers SID International Symposium, 2019, 50, 1011-1014.	0.3	2
16	A {c}\$ -Axis-Aligned Crystalline In-Ga-Zn Oxide FET With a Gate Length of 21 nm Suitable for Memory Applications. IEEE Journal of the Electron Devices Society, 2019, 7, 495-502.	2.1	17
17	Crystalline <sc>IGZO</sc> ceramics (crystalline oxide semiconductor)â€based devices for artificial intelligence. International Journal of Ceramic Engineering & Science, 2019, 1, 6-20.	1.2	17
18	OLED display incorporating organic photodiodes for fingerprint imaging. Journal of the Society for Information Display, 2019, 27, 361-371.	2.1	19

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19	3D-Stacked CAAC-In-Ga-Zn Oxide FETs with Gate Length of 72nm. , 2019, , .		15
20	A 20ns-write 45ns-read and 10 ¹⁴ -cycle endurance memory module composed of 60nm crystalline oxide semiconductor transistors. , 2018, , .		7
21	High thermal tolerance of 25-nm c-axis aligned crystalline In-Ga-Zn oxide FET. , 2018, , .		20
22	50 ³ : Formation of Source and Drain Regions in Top ² -Gate Self ¹ -Aligned Oxide Semiconductor Field ¹ -Effect Transistor. Digest of Technical Papers SID International Symposium, 2018, 49, 660-663.	0.3	4
23	24 ¹ : <i>Invited Paper</i>: Flexible OLED Display Using C ¹ -Axis ¹ -Aligned ¹ -Crystal/Cloud ¹ -Aligned Composite Oxide Semiconductor Technology and Laser Separation Technology. Digest of Technical Papers SID International Symposium, 2017, 48, 329-332.	0.3	7
24	Embedded Memory and ARM Cortex-M0 Core Using 60-nm C-Axis Aligned Crystalline Indium ¹ -Gallium ¹ -Zinc Oxide FET Integrated With 65-nm Si CMOS. IEEE Journal of Solid-State Circuits, 2017, 52, 925-932.	5.4	30
25	76 ² : Field ¹ -Effect Transistor with CAAC/CAC ¹ OS Double ¹ -Layer Structure for Diversion of Gen 8 ¹ to 10.5 Amorphous Silicon Production Lines. Digest of Technical Papers SID International Symposium, 2017, 48, 1112-1115.	0.3	0
26	A 140 MHz 1 Mbit 2T1C gain-cell memory with 60-nm indium-gallium-zinc oxide transistor embedded into 65-nm CMOS logic process technology. , 2017, , .		12
27	A 25.3 $\mu\text{m} \times 160\mu\text{m}$ at 60 fps $160\mu\text{m} \times 160\mu\text{m}$ Pixel Vision Sensor for Motion Capturing With In-Pixel Nonvolatile Analog Memory Using CAAC-IGZO FET. IEEE Journal of Solid-State Circuits, 2016, 51, 2168-2179.	5.4	4
28	Embedded memory and ARM Cortex-M0 core using 60-nm C-axis aligned crystalline indium-gallium-zinc oxide FET integrated with 65-nm Si CMOS. , 2016, , .		22
29	A foldable OLED display with an in-cell touch sensor having embedded metal-mesh electrodes. Journal of the Society for Information Display, 2016, 24, 12-20.	2.1	20
30	Achievement of a high-mobility FET with a cloud-aligned composite oxide semiconductor. Japanese Journal of Applied Physics, 2016, 55, 115504.	1.5	18
31	A 16-level-cell memory with c-axis-aligned a ¹ -b-plane-anchored crystal In ¹ -Ga ¹ -Zn oxide FET using threshold voltage cancel write method. Japanese Journal of Applied Physics, 2016, 55, 04EE02.	1.5	3
32	Correlation between crystallinity and oxygen vacancy formation in In ¹ -Ga ¹ -Zn oxide. Japanese Journal of Applied Physics, 2016, 55, 021203.	1.5	19
33	Fabrication of dynamic oxide semiconductor random access memory with 3.9 fF storage capacitance and greater than 1 h retention by using c ¹ -axis aligned crystalline oxide semiconductor transistor with L ¹ of 60 nm. Japanese Journal of Applied Physics, 2015, 54, 04DD07.	1.5	7
34	Influence of heat treatment on physical properties of In ¹ -Ga ¹ -Zn ¹ -O thin films. Japanese Journal of Applied Physics, 2015, 54, 04DH12.	1.5	2
35	18.3: An 8.67 μm In ¹ -Cell Touch Sensor. Digest of Technical Papers SID International Symposium, 2015, 46, 246-249.	0.3	27
36	Channel length dependence of field-effect mobility of c ¹ -axis-aligned crystalline In ¹ -Ga ¹ -Zn ¹ -O field-effect transistors. Japanese Journal of Applied Physics, 2015, 54, 041103.	1.5	13

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37	Back-channel-etched thin-film transistor using c-axis-aligned crystal InGaZn oxide. Journal of the Society for Information Display, 2014, 22, 55-67.	2.1	51
38	Embedded SRAM and Cortex-M0 Core Using a 60-nm Crystalline Oxide Semiconductor. IEEE Micro, 2014, 34, 42-53.	1.8	14
39	Properties of crystalline InGaZn-oxide semiconductor and its transistor characteristics. Japanese Journal of Applied Physics, 2014, 53, 04ED18.	1.5	71
40	Single crystalline InGaZn oxide films grown from c-axis aligned crystalline materials and their transistor characteristics. Japanese Journal of Applied Physics, 2014, 53, 091102.	1.5	30
41	Nonvolatile Memory With Extremely Low-Leakage Indium-Gallium-Zinc-Oxide Thin-Film Transistor. IEEE Journal of Solid-State Circuits, 2012, 47, 2258-2265.	5.4	76
42	15.1: Research, Development, and Application of Crystalline Oxide Semiconductor. Digest of Technical Papers SID International Symposium, 2012, 43, 183-186.	0.3	163
43	1Mb Non-Volatile Random Access Memory Using Oxide Semiconductor. , 2011, , .		21
44	28.2: Color Sequential LC Display Using High Reliable Oxide Semiconductors with Monochrome Electronic Paper Function. Digest of Technical Papers SID International Symposium, 2011, 42, 369-372.	0.3	32
45	Low Power 6.0-inch Extended Graphics Array Transmissive Liquid Crystal Display using Indium Gallium Zinc Oxide Semiconductor with Variable Frame Frequency. ECS Transactions, 2011, 37, 97-103.	0.5	4
46	6.0-Inch Extended Graphics Array Reflective Liquid Crystal Display Using Oxide Semiconductor Thin Film Transistors for Electronic Paper Display. Japanese Journal of Applied Physics, 2011, 50, 03CC09.	1.5	16